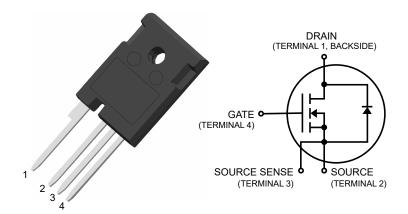
1200V, 25 mΩ N-Channel mSiC[™] MOSFET

MSC025SMA120B4N



Product Overview

1200V, 25 m Ω typical at V_{GS} = 20V, 28 m Ω typical at V_{GS} = 18V, Silicon Carbide (SiC) N-Channel MOSFET, TO-247 notched 4-lead with a source sense.



Features

- AEC-Q101 qualified option available
- Low capacitances and low gate charge
- Fast switching speed due to low internal gate resistance (ESR)
- Stable operation at high junction temperature, T_{I(max)} = 175 °C
- · Fast and reliable body diode
- Superior avalanche ruggedness
- · RoHS compliant

Benefits

- High efficiency to enable lighter and more compact system
- Simple to drive and easy to parallel
- Improved thermal capabilities and lower switching losses
- Eliminates the need for external freewheeling diode
- · Lower system cost of ownership

Applications

- Photovoltaic (PV) inverter, converter, and industrial motor drives
- Smart grid transmission and distribution
- · Induction heating and welding
- Hybrid Electric Vehicle (HEV) powertrain and Electric Vehicle (EV) charger
- Power supply and distribution

1. Device Specifications

This section shows the specifications of this device.

1.1 Absolute Maximum Ratings

The following table shows the absolute maximum ratings of this device.

Table 1-1. Absolute Maximum Ratings

Symbol	Parameter	Ratings	Unit
V_{DSS}	Drain source voltage	1200	V
I _D	Continuous drain current at T _C = 25 °C	113	A
	Continuous drain current at T _C = 100 °C	80	
I _{DM}	Pulsed drain current ¹	408	
V_{GS}	Gate-source voltage	23 to -10	V
	Transient gate-source voltage	25 to -12	
P _D	Total power dissipation at T _C = 25 °C	577	W
	Linear derating factor	3.8	W/°C

Note:

1. Repetitive rating: pulse width and case temperature are limited by the maximum junction temperature.

The following table shows the thermal and mechanical characteristics of this device.

Table 1-2. Thermal and Mechanical Characteristics

Symbol	Characteristic/Test Conditions	Min.	Тур.	Max.	Unit
$R_{\theta JC}$	Junction-to-case thermal resistance	_	0.20	0.26	°C/W
T _J	Operating junction temperature	-55	_	175	°C
T _{STG}	Storage temperature	-55	_	175	
T _L	Lead temperature for 10 seconds	_	_	300	°C
τ_{M}	Mounting torque, M3 screw for heat sink attachment (requires 1, not included)	_	0.8	_	N-m
Wt	Package weight	_	6.2	_	g

ESD practices should comply with JESD-625.

1.2 Electrical Performance

The following table shows the static characteristics of this device. $T_J = 25$ °C unless otherwise specified.

Table 1-3. Static Characteristics

Symbol	Characteristic	Test Conditions	Min.	Тур.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown voltage	$V_{GS} = 0V$, $I_D = 100 \mu A$	1200	_	_	V
R _{DS(on)}	Drain-source on resistance ¹	$V_{GS} = 20V, I_D = 40A$	_	25	31	mΩ
		V _{GS} = 18V, I _D = 40A	_	28	_	
V _{GS(th)}	Gate-source threshold voltage	$V_{GS} = V_{DS}$, $I_D = 3 \text{ mA}$	1.9	3.0	5.0	V
I _{DSS}	Zero gate voltage drain current	V _{DS} = 1200V, V _{GS} = 0V	_	0.3	35	μΑ
		V _{DS} = 1200V, V _{GS} = 0V, T _J = 175 °C	_	3.5	_	
I _{GSS}	Gate-source leakage current	V _{GS} = 20V/–10V	_	_	±100	nA



Note:

1. Pulse test: pulse width < 380 μ s, duty cycle < 2%.

The following table shows the dynamic characteristics of this device. T_J = 25 °C unless otherwise specified. The dynamic characteristics are characterized, not 100% tested, at the recommended operating V_{GS} = 20V/–5V.

Table 1-4. Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min.	Тур.	Max.	Unit
C _{iss}	Input capacitance	V _{GS} = 0V	_	3633	_	pF
C _{rss}	Reverse transfer capacitance	V _{DD} = 1000V	_	18	_	
C _{oss}	Output capacitance	$V_{AC} = 25 \text{ mV}$ f = 200 KHz	_	271	_	
Q_{G}	Total gate charge	V _{GS} = -5V/20V	_	232	_	nC
Q_{GS}	Gate-source charge	V _{DD} = 800V	_	41	_	
Q_{GD}	Gate-drain charge	I _D = 40A	_	50	_	
t _{d(on)}	Turn-on delay time	V _{DD} = 800V	_	17	_	ns
t _r	Voltage rise time	$V_{GS} = -5V/20V$	_	23	_	
t _{d(off)}	Turn-off delay time	I _D = 40A	_	39	_	
t _f	Voltage fall time	$R_{G(ext)} = 4\Omega$	_	16	_	
E _{on}	Turn-on switching energy	Freewheeling diode = MSC025SMA120B4N (V _{GS} = -5V);	_	716	_	μJ
E _{off}	Turn-off switching energy	reference Figure 1-19	_	98	_	
ESR	Gate equivalent series resistance	f = 1 MHz, 25 mV, drain short	_	0.88	_	Ω
SCWT	Short circuit withstand time	V _{DS} = 960V, V _{GS} = 20V	_	3	_	μs
E _{AS}	Avalanche energy, single pulse	I _D = 40A	_	3500	_	mJ

The following table shows the body diode characteristics of this device. $T_J = 25$ °C unless otherwise specified. The body diode reverse recovery is characterized, not 100% tested.

Table 1-5. Body Diode Characteristics

Symbol	Characteristic	Test Conditions	Min.	Тур.	Max.	Unit
V_{SD}	Diode forward voltage	$I_{SD} = 40A$, $V_{GS} = 0V$	_	3.6	_	V
		$I_{SD} = 40A, V_{GS} = -5V$	_	3.8	5.0	
t _{rr}	Reverse recovery time	I_{SD} = 40A, V_{GS} = –5V, Drive R_G = 4 Ω , V_{DD} =	_	15	_	ns
Q _{rr}	Reverse recovery charge	800V, dI/dt = –10000 A/μs	_	995	_	nC
I _{RRM}	Reverse recovery current		_	112	_	Α



1.3 Typical Performance Curves

Data for performance curves are characterized, not 100% tested.

Figure 1-1. Drain Current vs. V_{DS} at T_J

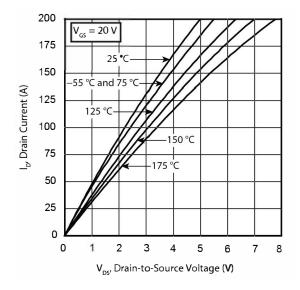


Figure 1-2. Drain Current vs. V_{DS} at V_{GS}

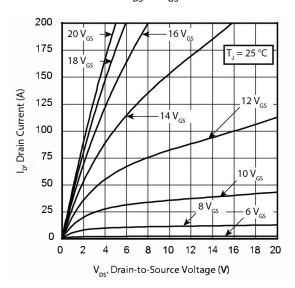


Figure 1-3. Drain Current vs. V_{DS} at V_{GS}

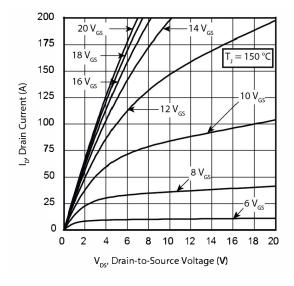


Figure 1-4. Drain Current vs. V_{DS} at V_{GS}

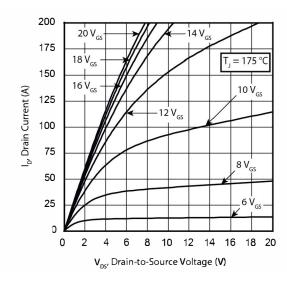




Figure 1-5. R_{DS(on)} vs. Junction Temperature

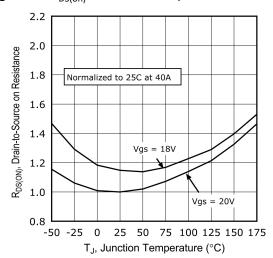


Figure 1-6. Gate Charge Characteristics

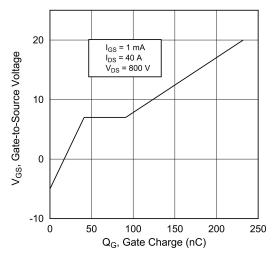


Figure 1-7. Capacitance vs. Drain-to-Source Voltage

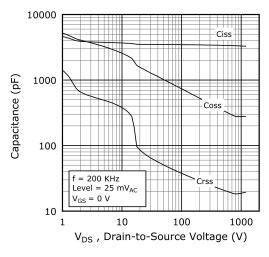


Figure 1-8. Output Charge vs. Drain-to-Source Voltage

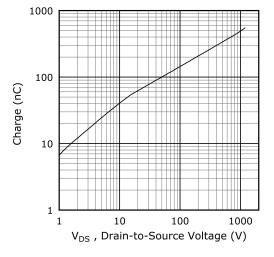




Figure 1-9. Output Stored Energy vs. V_{DS}

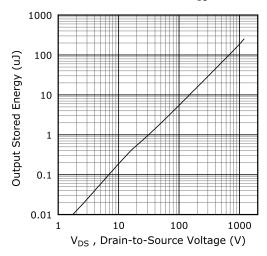


Figure 1-11. I_D vs. V_{DS} 3rd Quadrant Conduction

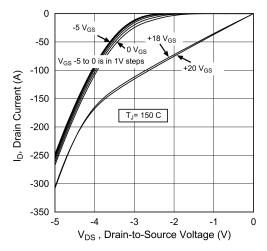


Figure 1-10. I_D vs. V_{DS} 3^{rd} Quadrant Conduction

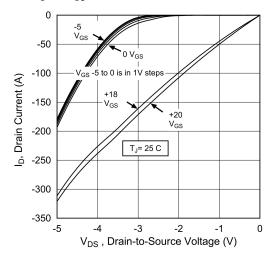


Figure 1-12. Switching Energy E_{on} vs. $V_{DS} \& I_{D}$

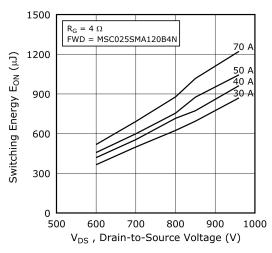




Figure 1-13. Switching Energy E_{off} vs. $V_{DS} \& I_{D}$

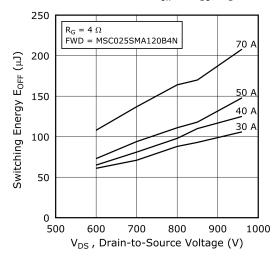


Figure 1-14. Switching Energy vs. R_G

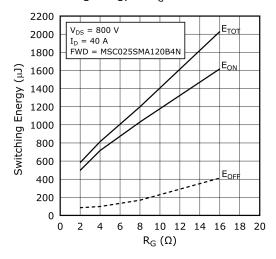


Figure 1-15. Switching Energy vs. Junction Temperature

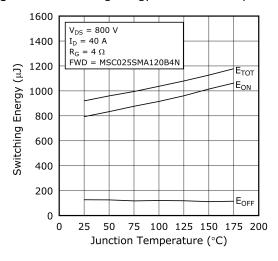


Figure 1-16. Threshold Voltage vs. Junction Temperature

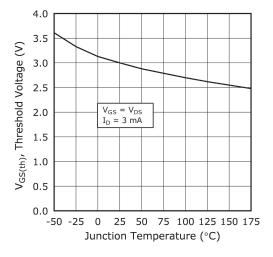




Figure 1-17. Forward Safe Operating Area

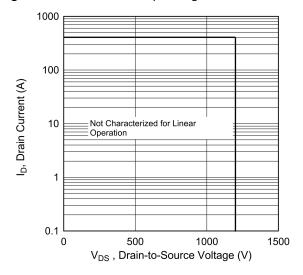
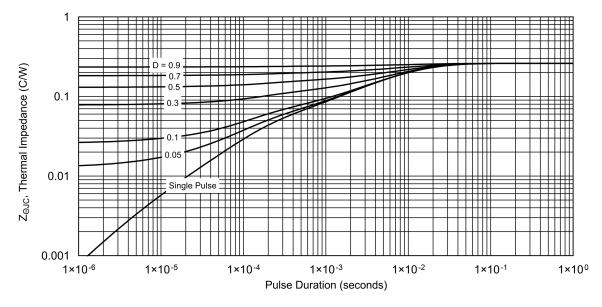
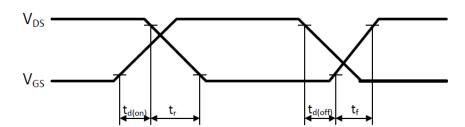


Figure 1-18. Maximum Transient Thermal Impedance



The following figure shows the switching waveform diagram of this device.

Figure 1-19. Switching Waveform





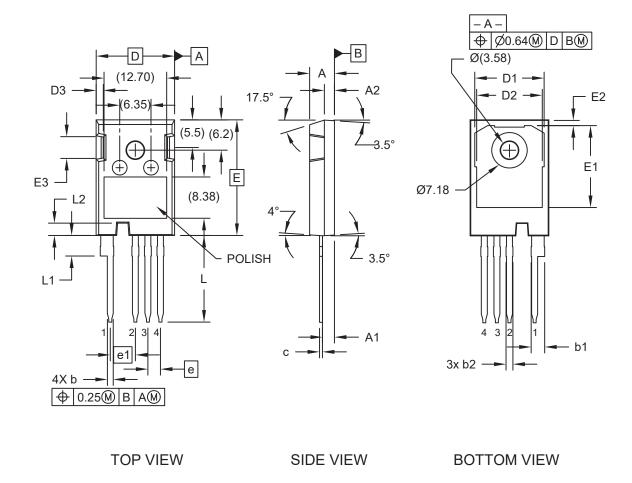
2. Package Specification

This section shows the package specification of this device.

2.1 Package Outline Drawing

The following figure illustrates the TO-247 notched-4L package outline of this device.

Figure 2-1. Package Outline Drawing



The following table shows the TO-247 notched-4L dimensions and should be used in conjunction with the package outline drawing.

Table 2-1. TO-247 Notched-4L Dimensions

Symbol	Description	Min. (mm)	Nom. (mm)	Max. (mm)
N	Number of terminals	4		
е	Pitch	2.54 BSC		
e1		5.08 BSC		
Α	Overall height	4.83	5.02	5.21
A1	Standoff	2.29	2.41	2.54
A2	Exposed pad thickness	1.91	2.03	2.16
С	Terminal thickness	0.55	0.60	0.68
D	Overall length	15.75	15.94	16.13



continued					
Symbol	Description	Min. (mm)	Nom. (mm)	Max. (mm)	
D1	Exposed pad length	13.10	13.62	14.15	
D2		12.38	12.90	13.43	
D3	Cutout length	1.00	1.45	1.90	
E	Overall width	23.30	23.45	23.60	
E1	Exposed pad width	16.25	16.95	17.65	
E2	Exposed pad gap to edge	0.95	1.10	1.25	
E3	Cutout width	3.68	4.39	5.10	
b	Terminal width	1.07	1.20	1.33	
b1	Terminal shoulder width (X1)	2.39	2.66	2.94	
b2	Terminal shoulder width (X3)	1.07	1.33	1.60	
L	Terminal length	17.31	17.56	17.82	
L1	Terminal shoulder length	3.97	4.17	4.37	
L2	Notch depth	2.35	2.50	2.65	

Note:

Dimensioning and tolerancing per ASME Y14.5M.

• BSC: Basic dimension. Theoretically exact value shown without tolerances.



3. Revision History

The revision history describes the changes that were implemented in the document. The changes are listed by revision, starting with the most current publication.

Table 3-1. Revision History

Revision	Date	Description	
В	07/2024	The following changes are made in this revision of the document:	
		 Added AEC feature in Product Overview. 	
		• Updated T _{STG} value in Table 1-2.	
		• Updated mounting torque row in Table 1-2.	
A	02/2024	Initial revision	



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HC1M320120D HC2M0045170P HC1M30065D HC1M60120D HC2M0650170D HC1M40120D SC060N065T8L SC015N065TCL

SC013N120TCL SC021N120T8L SC032N120T8L YJD212080NCTG1 YJD212040NCFG2 SC015N065T8L SC160N120T8L

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DMWSH120H28SM3 DMWSH120H28SM3Q DMWSH120H90SM3Q DIF065SIC020 DIF120SIC022-AQ DIF065SIC030